Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) An electronic device comprising: ~~a nonvolatile memory, wherein the nonvolatile memory comprises a memory element, and wherein the memory element comprises a first thin film transistor comprising a floating gate and a second thin film transistor~~

a pixel region including a first thin film transistor over a substrate;

a source signal line side driver operationally connected to the pixel region, said source signal line side driver comprising a second thin film transistor over the substrate;

a gamma correction control circuit operationally connected to the source signal line side driver, said gamma correction control circuit comprising a third thin film transistor over the substrate; and

a nonvolatile memory operationally connected to the gamma correction control circuit, said nonvolatile memory comprising a fourth thin film transistor over the substrate.

2.-20. (Cancelled)

21. (New) The electronic device according to claim 1 wherein each of the first, second and third thin film transistors comprises a first semiconductor layer formed on an insulating surface over the substrate and a first gate electrode over the first semiconductor layer with a first gate insulator interposed therebetween while said fourth thin film transistor comprises a second semiconductor layer formed on said insulating surface, a second gate electrode over the second semiconductor layer with a second gate insulator interposed therebetween and a third gate electrode formed over the second gate electrode, said second gate electrode being electrically floating.

22. (New) The electronic device according to claim 1 wherein said electronic device is a portable phone.

23. (New) The electronic device according to claim 1 wherein said electronic device is a camera.

24. (New) The electronic device according to claim 1 wherein said electronic device is a mobile computer.

25. (New) An electronic device comprising:

a matrix of first thin film transistors over a substrate;

a source signal line side driver operationally connected to the matrix of first thin film transistors, said source signal line side driver comprising a second thin film transistor over the substrate;

a correction control circuit operationally connected to the source signal line side driver, said gamma correction control circuit comprising a third thin film transistor over the substrate; and

a nonvolatile memory operationally connected to the gamma correction control circuit, said nonvolatile memory comprising a fourth thin film transistor over the substrate.

26. (New) The electronic device according to claim 25 wherein each of the first, second and third thin film transistors comprises a first semiconductor layer formed on an insulating surface over the substrate and a first gate electrode over the first semiconductor layer with a first gate insulator interposed therebetween while said fourth thin film transistor comprises a second semiconductor layer formed on said insulating surface, a second gate electrode over the second semiconductor layer with a second gate insulator interposed therebetween and a third gate electrode formed over the second gate electrode, said second gate electrode being electrically floating.

27. (New) The electronic device according to claim 26 wherein said electronic device is a portable phone.

28. (New) The electronic device according to claim 26 wherein said electronic device is a camera.

29. (New) The electronic device according to claim 26 wherein said electronic device is a mobile computer.

30. (New) The electronic device of claim 26 wherein a data is applied from the nonvolatile memory to the gamma correction control circuit through a D/A conversion circuit.

31. (New) An electronic device comprising:

a pixel region including a first thin film transistor over a substrate;

a source signal line side driver operationally connected to the pixel region, said source signal line side driver comprising a second thin film transistor over the substrate;

a gamma correction control circuit operationally connected to the source signal line side driver, said gamma correction control circuit comprising a third thin film transistor over the substrate; and

a nonvolatile memory operationally connected to the gamma correction control circuit through at least first route and a second route, said nonvolatile memory comprising a fourth thin film transistor over the substrate,

wherein said first route comprises an A/D conversion circuit and said second route comprises a D/A conversion circuit.

32. (New) The electronic device according to claim 31 wherein each of the first, second and third thin film transistors comprises a first semiconductor layer formed on an insulating surface over the substrate and a first gate electrode over the first semiconductor layer with a first gate insulator interposed therebetween while said fourth thin film transistor comprises a second semiconductor layer formed on said insulating surface, a second gate electrode over the second semiconductor layer with a second gate insulator interposed therebetween and a third gate electrode formed over the second gate electrode, said second gate electrode being electrically floating.

33. (New) The electronic device according to claim 31 wherein said electronic device is a portable phone.

34. (New) The electronic device according to claim 31 wherein said electronic device is a camera.

35. (New) The electronic device according to claim 31 wherein said electronic device is a mobile computer.

36. (New) An electronic device comprising:

a matrix of first thin film transistors over a substrate;

a source signal line side driver operationally connected to the matrix of first thin film transistors, said source signal line side driver comprising a second thin film transistor over the substrate;

a correction control circuit operationally connected to the source signal line side driver, said gamma correction control circuit comprising a third thin film transistor over the substrate; and

a nonvolatile memory operationally connected to the gamma correction control circuit through at least a first route and a second route, said nonvolatile memory comprising a fourth thin film transistor over the substrate,

wherein said first route comprises an A/D conversion circuit and said second route comprises a D/A conversion circuit.

37. (New) The electronic device according to claim 36 wherein each of the first, second and third thin film transistors comprises a first semiconductor layer formed on an insulating surface over the substrate and a first gate electrode over the first semiconductor layer with a first gate insulator interposed therebetween while said fourth thin film transistor comprises a second semiconductor layer formed on said insulating surface, a second gate electrode over the second semiconductor layer with a second gate insulator interposed

therebetween and a third gate electrode formed over the second gate electrode, said second gate electrode being electrically floating.

38. (New) The electronic device according to claim 36 wherein said electronic device is a portable phone.

39. (New) The electronic device according to claim 36 wherein said electronic device is a camera.

40. (New) The electronic device according to claim 36 wherein said electronic device is a mobile computer.

41. (New) The electronic device of claim 36 wherein a data is applied from the nonvolatile memory to the gamma correction control circuit through a D/A conversion circuit.

42. (New) An electronic device comprising:

a pixel region including a first thin film transistor over a substrate;

a source signal line side driver operationally connected to the pixel region, said source signal line side driver comprising a second thin film transistor over the substrate;

a gamma correction control circuit operationally connected to the source signal line side driver, said gamma correction control circuit comprising a third thin film transistor over the substrate; and

a nonvolatile memory operationally connected to the gamma correction control circuit through at least a volatile memory.

43. (New) The electronic device according to claim 42 wherein each of the first, second and third thin film transistors comprises a first semiconductor layer formed on an insulating surface over the substrate and a first gate electrode over the first semiconductor layer with a first gate insulator interposed therebetween while said fourth thin film transistor comprises a second semiconductor layer formed on said insulating surface, a second gate

electrode over the second semiconductor layer with a second gate insulator interposed therebetween and a third gate electrode formed over the second gate electrode, said second gate electrode being electrically floating.

44. (New) The electronic device according to claim 42 wherein said electronic device is a portable phone.

45. (New) The electronic device according to claim 42 wherein said electronic device is a camera.

46. (New) The electronic device according to claim 42 wherein said electronic device is a mobile computer.

47. (New) An electronic device comprising:

a matrix of first thin film transistors over a substrate;

a source signal line side driver operationally connected to the matrix of first thin film transistors, said source signal line side driver comprising a second thin film transistor over the substrate;

a correction control circuit operationally connected to the source signal line side driver, said gamma correction control circuit comprising a third thin film transistor over the substrate; and

a nonvolatile memory operationally connected to the gamma correction control circuit through at least a volatile memory.

48. (New) The electronic device according to claim 47 wherein each of the first, second and third thin film transistors comprises a first semiconductor layer formed on an insulating surface over the substrate and a first gate electrode over the first semiconductor layer with a first gate insulator interposed therebetween while said fourth thin film transistor comprises a second semiconductor layer formed on said insulating surface, a second gate electrode over the second semiconductor layer with a second gate insulator interposed

therebetween and a third gate electrode formed over the second gate electrode, said second gate electrode being electrically floating.

49. (New) The electronic device according to claim 48 wherein said volatile memory comprises a fifth thin film transistor formed on said insulating surface.

50. (New) The electronic device according to claim 47 wherein said electronic device is a portable phone.

51. (New) The electronic device according to claim 47 wherein said electronic device is a camera.

52. (New) The electronic device according to claim 47 wherein said electronic device is a mobile computer.